



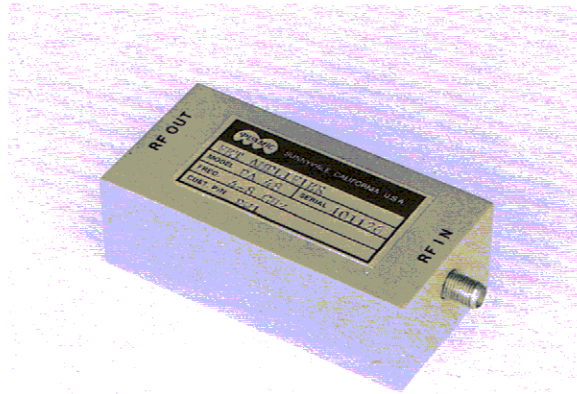
# FET AMPLIFIERS

## FEATURES

- Low cost
- Drift-free
- Wide temperature range
- Rugged

## DESCRIPTION:

The PLAMIC GaAs FET Amplifiers are multistage units using the latest transistor chips and MIC (Microwave Integrated Circuit) interstage and impedance matching sections. Transistors are selected for optimum noise and gain characteristics, and freedom from both short and long-term drift. MIC sections utilize thin-film gold conductors on high purity alumina substrates. Active bias circuits provide for gain stability and Kovar carriers yield mechanical integrity over wide temperature variations.



## APPLICATIONS:

These amplifiers are ideal for a wide variety of applications, including TWTA replacements, ECM systems (both are airborne and surface), telecommunications systems, radar applications, ESM systems and others. They can easily be integrated with other microwave components, such as filters, switches, signal distribution networks, etc., to form a single integrated subsystem.

## TYPICAL SPECIFICATIONS:

These amplifiers are available in bandwidths of 5% to 70%, in both single-ended or balanced configuration, from 3 to 15 GHz. Typical characteristics for wideband amplifiers are:

<b>Frequency:</b>	4-8 GHz	6-12 GHz
<b>VSWR:</b>	1.7:1 maximum, input and output	2:1 maximum, input and output
<b>Noise Figure:</b>	6 dB maximum	7 dB maximum
<b>Gain:</b>	25 dB	25 dB
<b>Gain Flatness:</b>	±1 dB	±1.5 dB
<b>1 dB Compression Point:</b>	+10 dBm minimum	+9 dBm min.
<b>Size:</b>	3.5"x1"x1.5"	3.5" x 1" x 1.5"

## PLAMIC MEANS MIC

For further information please contact:

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